

B²
15. (Amended) The method of claim 30, wherein the first gas is a non-reactive gas.

B³
17. (Amended) The method of claim 30, wherein the second plasma includes HBr plasma gas.

18. (Amended) The method of claim 30, wherein the second plasma includes a composition of HBr plasma gas and Cl₂ plasma gas.

19. (Amended) The method of claim 30, wherein the second plasma includes a composition of HBr plasma gas and CH₄ plasma gas.

20. (Amended) The method of claim 30, wherein the metal layer includes one of indium tin oxide (ITO) and indium zinc oxide (IZO).

21. (Amended) The method of claim 30, further comprising:
removing the photoresist pattern from the pixel electrode.

Please add new claim 30 as follows:

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--30. (New) A method of manufacturing a pixel electrode in a liquid crystal display device, comprising:

depositing a metal layer on a passivation layer which partially covers a transistor;

forming a photoresist pattern on the metal layer, leaving a portion of the metal layer uncovered;

exposing the uncovered portion of the metal layer to at least one first gas, } prior to etching, to lower a binding force in the uncovered portion; and

etching the uncovered portion of the metal layer with at least one second gas to form a pixel electrode.--
